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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 2 of 2

Complete if Known

Application Number	
Filing Date	December 1, 2003
First Named Inventor	Crocifisso Marco Antonio Renna
Group Art Unit	
Examiner Name	
Attorney Docket Number	2110-91-3

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MDH		European Search Report for 02425742.0 dated August 6, 2003	
		Tsunashima, et al. "A New Substrate Engineering Technique to Realize Silicon on Nothing" Electrochemical Society Proceedings, Electrochemical Society, Pennington, NJ, US, No. 17, 2000, pp. 532-545, XP008004134 ISSN: 0161-8374	
↓		Sato, et al. "SON (silicon on nothing) MOSFET Using ESS (empty space in silicon) Technique for SoC Applications" International Electron Devices Meeting 2001. IEDM. Technical Digest. Washington, DC, Dec. 2-5, 2001, New York, NY: IEEE, U.S., 2 December 2001, pp. 3771-3774, XP010575245 ISBN: 0-7803-7050-3	

Examiner Signature	<i>Monica D. Plamen</i>	Date Considered	10/13/05
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